

# iscN-Channel MOSFET Transistor

## IRFRC20

## • FEATURES

- Low drain-source on-resistance: R<sub>DS</sub>(ON) =4.4Ω (MAX)
- · Enhancement mode:
  - Vth = 2.0 to 4.0V (VDs = 10 V, ID=0.25mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

Switching Voltage Regulators

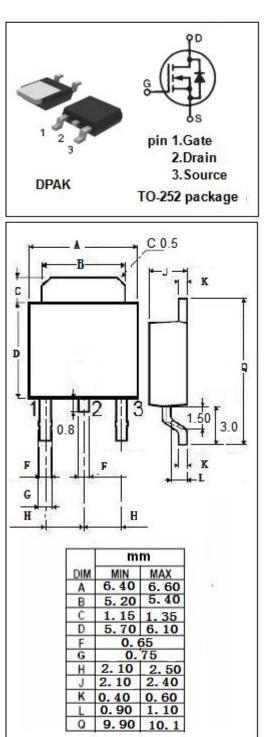
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

PARAMETER	VALUE	UNIT
Drain-Source Voltage	600	V
Gate-Source Voltage	±20	V
Drain Current-Continuous	2.0	А
Drain Current-Single Pulsed	8.0	А
Total Dissipation @T <sub>C</sub> =25℃	42	W
Max. Operating Junction Temperature	nction Temperature -55~150	
Storage Temperature -55~150		°C
-	Drain-Source Voltage Gate-Source Voltage Drain Current-Continuous Drain Current-Single Pulsed Total Dissipation @Tc=25°C Max. Operating Junction Temperature	Drain-Source Voltage600Gate-Source Voltage±20Drain Current-Continuous2.0Drain Current-Single Pulsed8.0Total Dissipation @Tc=25°C42Max. Operating Junction Temperature-55~150

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	3.0	°C/W

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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\texttt{C}}\text{=}25^{\circ}\!\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA	600			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = 10V; I <sub>D</sub> =0.25mA	2.0		4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =1.2A			4.4	Ω
lgss	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V V <sub>DS</sub> =480V; V <sub>GS</sub> = 0V;T <sub>J</sub> =125℃			100 500	uA
V <sub>SDF</sub>	Diode forward voltage	I <sub>DR</sub> =2.0A, V <sub>GS</sub> = 0 V			1.6	V

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